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**PATENT**  
Attorney Docket No.: ASC-066

THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANTS: Westhoff et al  
SERIAL NO.: 10/765,372 GROUP NO.: 2812  
FILING DATE: January 27, 2004 EXAMINER: Not yet assigned  
TITLE: SEMICONDUCTOR STRUCTURES WITH STRUCTURAL HOMOGENEITY

Mail Stop Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT**

Sir:

In accordance with the provisions of 37 C.F.R. 1.97 and 1.98, Applicants hereby make of record the patents and publications listed on the accompanying Form PTO-1449, and other information contained herein, for consideration by the Examiner in connection with the examination of the above-identified patent application. In accordance with the U.S. Patent Office's partial waiver of the requirement under 37 C.F.R. 1.98(a)(2)(i), only copies of the non-U.S. patent publications are enclosed.

**REMARKS**

In accordance with the provisions of 37 C.F.R. 1.97, this statement is being filed (CHECK ONE):

(1) within three (3) months of the **filin** **g date** of a national application other than a continued prosecution application under 37 C.F.R. 1.53(d), or within three (3) months of the **date of entry of the national stage** as set forth in 37 C.F.R. 1.491 in an international application, or before the mailing of the **first Office action** on the merits, or before the mailing of a **first Office action** after the filing of a request for continued examination under 37 C.F.R. 1.114; or

(2) after the period defined in (1) but before the mailing date of a **final action** or a **notice of allowance** under 37 C.F.R. 1.311, and

the requisite Statement is below, OR

Supplemental Information Disclosure Statement

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- the requisite fee under 37 C.F.R. 1.17(p), namely **\$180.00**, is included herein, or
- (3) after the mailing date of a **final action or notice of allowance** but before the payment of the **issue fee**, **AND**
- the requisite Statement is below, **AND**
- the requisite petition fee under 37 C.F.R. 1.17(p), namely **\$180.00** is included herein.

It is respectfully requested that each of the patents and publications listed on the attached Form PTO-1449, and other information contained herein, be made of record in this application.

Respectfully submitted,

Date: December 15, 2004  
Reg. No. 44,381

Tel. No.: (617) 310-8327  
Fax No.: (617) 248-7100

*Natasha C. Us*  
\_\_\_\_\_  
Natasha C. Us  
Attorney for the Applicants  
Testa, Hurwitz, & Thibeault, LLP  
High Street Tower  
125 High Street  
Boston, Massachusetts 02110



# TRANSMITTAL FORM

Application Serial Number	10/765,372
Filing Date	January 27, 2004
First Named Inventor	Westhoff
Group Art Unit	2812
Examiner Name	Not yet assigned
Attorney Docket No.	ASC-066
Patent No.	Not applicable
Issue Date	Not applicable

## ENCLOSURES (check all that apply)

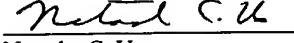
<input type="checkbox"/> Fee Transmittal Form <ul style="list-style-type: none"> <li><input type="checkbox"/> Check Attached</li> <li><input type="checkbox"/> Copy of Fee Transmittal Form</li> </ul>	<input type="checkbox"/> Copy of Notice to File Missing Parts of Application <ul style="list-style-type: none"> <li><input type="checkbox"/> Formal Drawing(s)</li> </ul>	<input type="checkbox"/> Notice of Appeal to Board of Patent Appeals and Interferences <ul style="list-style-type: none"> <li><input type="checkbox"/> Appeal Brief (in triplicate)</li> </ul>
<input type="checkbox"/> Amendment/Response <ul style="list-style-type: none"> <li><input type="checkbox"/> Preliminary</li> <li><input type="checkbox"/> After Final</li> <li><input type="checkbox"/> Affidavits/declaration(s)</li> <li><input type="checkbox"/> Letter to Official Draftsperson including Drawings [Total Sheets ____]</li> </ul>	<input type="checkbox"/> Request For Continued Examination (RCE) Transmittal <ul style="list-style-type: none"> <li><input type="checkbox"/> Power of Attorney (Revocation of Prior Powers)</li> </ul>	<input type="checkbox"/> Status Inquiry <ul style="list-style-type: none"> <li><input checked="" type="checkbox"/> Return Receipt Postcard</li> <li><input checked="" type="checkbox"/> Certificate of First Class Mailing under 37 C.F.R. 1.8</li> </ul>
<input type="checkbox"/> Petition for Extension of Time	<input type="checkbox"/> Terminal Disclaimer <ul style="list-style-type: none"> <li><input type="checkbox"/> Executed Declaration and Power of Attorney for Utility or Design Patent Application</li> </ul>	<input type="checkbox"/> Certificate of Facsimile Transmission under 37 C.F.R. 1.8 <ul style="list-style-type: none"> <li><input type="checkbox"/> Additional Enclosure(s) (please identify below)</li> </ul>
<input checked="" type="checkbox"/> Supplemental Information Disclosure Statement <ul style="list-style-type: none"> <li><input checked="" type="checkbox"/> Form PTO-1449</li> <li><input checked="" type="checkbox"/> Copies of IDS Citations B1-B50 and C2-C135</li> </ul>	<input type="checkbox"/> Small Entity Statement <ul style="list-style-type: none"> <li><input type="checkbox"/> CD(s) for large table or computer program</li> </ul>	
<input type="checkbox"/> Certified Copy of Priority Document(s)	<input type="checkbox"/> Amendment After Allowance <ul style="list-style-type: none"> <li><input type="checkbox"/> Request for Certificate of Correction</li> <li><input type="checkbox"/> Certificate of Correction (in duplicate)</li> </ul>	
<input type="checkbox"/> Sequence Listing submission <ul style="list-style-type: none"> <li><input type="checkbox"/> Paper Copy/CD</li> <li><input type="checkbox"/> Computer Readable Copy</li> <li><input type="checkbox"/> Statement verifying identity of above</li> </ul>		

## CORRESPONDENCE ADDRESS

Direct all correspondence to: Patent Administrator  
 Testa, Hurwitz & Thibeault, LLP  
 High Street Tower  
 125 High Street  
 Boston, MA 02110  
 Tel. No.: (617) 248-7000  
 Fax No.: (617) 248-7100

## SIGNATURE BLOCK

Respectfully submitted,

  
 Natasha C. Us  
 Attorney for Applicant(s)  
 Testa, Hurwitz & Thibeault, LLP  
 High Street Tower  
 125 High Street  
 Boston, MA 02110



PATENT  
Attorney Docket No. ASC-066

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

APPLICANTS: Westhoff *et al.*  
SERIAL NO.: 10/765,372 GROUP NO.: 2812  
FILING DATE: January 27, 2004 EXAMINER: Not yet assigned  
TITLE: SEMICONDUCTOR STRUCTURES WITH STRUCTURAL HOMOGENEITY

**CERTIFICATE OF FIRST CLASS MAILING UNDER 37 C.F.R. 1.8**

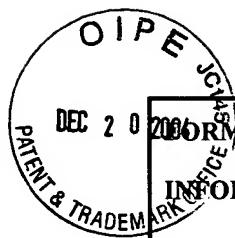
I hereby certify that this correspondence, and any document(s) referred to as enclosed herein, is/are being deposited with the United States Postal Service as first class mail, postage prepaid, in an envelope addressed to the Mail Stop Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on this 15<sup>th</sup> day of December, 2004.

Wendy Martin  
Wendy Martin

Mail Stop Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Submitted herewith are: Transmittal Form (1 page); Supplemental Information Disclosure Statement (2 pages); Form PTO-1449 (21 pages); copies of references B1-B50 and C2-C135; and a return receipt postcard.



2005 FORM PTO - 1449

## INFORMATION DISCLOSURE STATEMENT

ATTORNEY DOCKET NO.: ASC-066

APPLICANT(S): Westhoff *et al.*

SERIAL NO.: 10/765,372

FILING DATE: January 27, 2004 GROUP: 2812

## U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	A6	2001/0003364	06/14/2001	Sugawara <i>et al.</i>			
	A7	2001/0014570	08/16/2001	Wenski <i>et al.</i>			
	A8	2002/0043660	04/18/2002	Yamazaki <i>et al.</i>			
	A9	2002/0084000	07/04/2002	Fitzgerald			
	A10	2002/0096717	07/25/2002	Chu <i>et al.</i>			
	A11	2002/0100942	08/01/2002	Fitzgerald <i>et al.</i>			
	A12	2002/0123167	09/05/2002	Fitzgerald			
	A13	2002/0123183	09/05/2002	Fitzgerald			
	A14	2002/0125471	09/12/2002	Fitzgerald <i>et al.</i>			
	A15	2002/0168864	11/14/2002	Cheng <i>et al.</i>			
	A16	2002/0185686	12/12/2002	Christiansen <i>et al.</i>			
	A17	2003/0003679	01/02/2003	Doyle <i>et al.</i>			
	A18	2003/0013323	01/16/2003	Hammond <i>et al.</i>			
	A19	2003/0034529	02/20/2003	Fitzgerald <i>et al.</i>			
	A20	2003/0041798	03/06/2003	Wenski <i>et al.</i>			
	A21	2003/0057439	03/27/2003	Fitzgerald			
	A22	2003/0102498	06/05/2003	Braithwaite <i>et al.</i>			
	A23	2003/0199126	10/23/2003	Chu <i>et al.</i>			
	A24	2003/0203600	10/30/2003	Chu <i>et al.</i>			
	A25	2003/0215990	11/20/2003	Fitzgerald <i>et al.</i>			
	A26	2003/0218189	11/27/2003	Christiansen			
	A27	2003/0227057	12/01/2003	Lochtefeld <i>et al.</i>			
	A28	2004/0005740	01/01/2004	Lochtefeld <i>et al.</i>			
	A29	2004/0014304	01/22/2004	Bhattacharyya			
	A30	2004/0031979	02/19/2004	Lochtefeld			06/06/2003
	A31	2004/0041210	03/04/2004	Mouli			09/02/2003
EXAMINER				DATE CONSIDERED			

FORM PTO - 1449  INFORMATION DISCLOSURE STATEMENT		ATTORNEY DOCKET NO.: ASC-066  APPLICANT(S): Westhoff <i>et al.</i>  SERIAL NO.: 10/765,372  FILING DATE: January 27, 2004 GROUP: 2812					
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## U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	A32	2004/0075149	04/22/2004	Fitzgerald <i>et al.</i>			07/23/2003
	A33	4,010,045	03/01/1977	Ruehrwein			
	A34	4,710,788	12/01/1987	Dambkes <i>et al.</i>			
	A35	4,900,372	02/13/1990	Lee <i>et al.</i>			
	A36	4,987,462	01/22/1991	Kim <i>et al.</i>			
	A37	4,990,979	02/05/1991	Otto			
	A38	4,997,776	03/05/1991	Harame <i>et al.</i>			
	A39	5,013,681	05/07/1991	Godbey <i>et al.</i>			
	A40	5,091,767	02/25/1992	Bean <i>et al.</i>			
	A41	5,097,630	03/24/1992	Maeda <i>et al.</i>			
	A42	5,155,571	10/13/1992	Wang <i>et al.</i>			
	A43	5,159,413	10/27/1992	Calviello <i>et al.</i>			
	A44	5,166,084	11/24/1992	Pfiester			
	A45	5,177,583	01/05/1993	Endo <i>et al.</i>			
	A46	5,202,284	04/13/1993	Kamins <i>et al.</i>			
	A47	5,207,864	05/04/1993	Bhat <i>et al.</i>			
	A48	5,208,182	05/04/1993	Narayan <i>et al.</i>			
	A49	5,210,052	05/11/1993	Takasaki			
	A50	5,212,110	05/18/1993	Pfiester <i>et al.</i>			
	A51	5,221,413	06/22/1993	Brasen <i>et al.</i>			
	A52	5,240,876	08/31/1993	Gaul <i>et al.</i>			
	A53	5,241,197	08/31/1993	Murakami <i>et al.</i>			
	A54	5,250,445	10/05/1993	Bean <i>et al.</i>			
	A55	5,252,173	10/12/1993	Inoue			
	A56	5,279,687	01/18/1994	Tuppen <i>et al.</i>			
	A57	5,285,086	02/08/1994	Fitzgerald			
	A58	5,291,439	03/01/1994	Kauffmann <i>et al.</i>			
EXAMINER				DATE CONSIDERED			

<b>FORM PTO - 1449</b> <b>INFORMATION DISCLOSURE STATEMENT</b>		ATTORNEY DOCKET NO.: ASC-066 APPLICANT(S): Westhoff <i>et al.</i> SERIAL NO.: 10/765,372 FILING DATE: January 27, 2004 GROUP: 2812
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**U.S. PATENT DOCUMENTS**

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	A59	5,298,452	03/29/1994	Meyerson			
	A60	5,308,444	05/03/1994	Fitz <i>et al.</i>			
	A61	5,310,451	05/10/1994	Tejwani <i>et al.</i>			
	A62	5,316,958	05/31/1994	Meyerson			
	A63	5,346,848	09/13/1994	Grupen- Shemansky <i>et al.</i>			
	A64	5,374,564	12/20/1994	Bruel			
	A65	5,399,522	03/21/1995	Ohori			
	A66	5,413,679	05/09/1995	Godbey			
	A67	5,424,243	06/13/1995	Takasaki			
	A68	5,425,846	06/20/1995	Koze <i>et al.</i>			
	A69	5,426,069	06/20/1995	Selvakumar <i>et al.</i>			
	A70	5,426,316	06/20/1995	Mohammad			
	A71	5,442,205	08/15/1995	Brasen <i>et al.</i>			
	A72	5,461,243	10/24/1995	Ek <i>et al.</i>			
	A73	5,461,250	10/24/1995	Burghartz <i>et al.</i>			
	A74	5,462,883	10/31/1995	Dennard <i>et al.</i>			
	A75	5,476,813	12/19/1995	Naruse			
	A76	5,479,033	12/26/1995	Baca <i>et al.</i>			
	A77	5,484,664	01/16/1996	Kitahara <i>et al.</i>			
	A78	5,523,243	06/04/1996	Mohammad			
	A79	5,523,592	06/04/1996	Nakagawa <i>et al.</i>			
	A80	5,534,713	07/09/1996	Ismail <i>et al.</i>			
	A81	5,536,361	07/16/1996	Kondo <i>et al.</i>			
	A82	5,540,785	07/30/1996	Dennard <i>et al.</i>			
	A83	5,572,043	11/05/1996	Shimizu <i>et al.</i>			
	A84	5,596,527	01/21/1997	Tomioka <i>et al.</i>			
	A85	5,617,351	04/01/1997	Bertin <i>et al.</i>			
<b>EXAMINER</b>				<b>DATE CONSIDERED</b>			

<b>FORM PTO - 1449</b> <b>INFORMATION DISCLOSURE STATEMENT</b>				<b>ATTORNEY DOCKET NO.: ASC-066</b> <b>APPLICANT(S): Westhoff <i>et al.</i></b> <b>SERIAL NO.: 10/765,372</b> <b>FILING DATE: January 27, 2004 GROUP: 2812</b>			
<b>U.S. PATENT DOCUMENTS</b>							
<b>EXAM. INIT.</b>		<b>DOCUMENT NUMBER</b>	<b>DATE</b>	<b>NAME</b>	<b>CLASS</b>	<b>SUB CLASS</b>	<b>FILING DATE IF APPROPRIATE</b>
	A86	5,630,905	05/20/1997	Lynch <i>et al.</i>			
	A87	5,633,516	05/27/1997	Mishima			
	A88	5,659,187	08/01/1997	Legoues <i>et al.</i>			
	A89	5,683,934	11/04/1997	Candelaria			
	A90	5,698,869	12/16/1997	Yoshimi <i>et al.</i>			
	A91	5,714,777	02/03/1998	Ismail <i>et al.</i>			
	A92	5,728,623	03/17/1998	Mori			
	A93	5,739,567	04/14/1998	Wong			
	A94	5,759,898	06/02/1998	Ek <i>et al.</i>			
	A95	5,777,347	07/07/1998	Bartelink			
	A96	5,786,612	07/28/1998	Otani <i>et al.</i>			
	A97	5,786,614	07/28/1998	Chuang <i>et al.</i>			
	A98	5,792,679	08/11/1998	Nakato			
	A99	5,801,085	09/01/1998	Kim <i>et al.</i>			
	A100	5,808,344	09/15/1998	Ismail <i>et al.</i>			
	A101	5,810,924	09/22/1998	Legoues <i>et al.</i>			
	A102	5,828,114	10/27/1998	Kim <i>et al.</i>			
	A103	5,847,419	12/08/1998	Imai <i>et al.</i>			
	A104	5,859,864	01/12/1999	Jewell			
	A105	5,877,070	03/02/1999	Goesele <i>et al.</i>			
	A106	5,891,769	04/06/1999	Liaw <i>et al.</i>			
	A107	5,906,708	05/25/1999	Robinson <i>et al.</i>			
	A108	5,906,951	05/25/1999	Chu <i>et al.</i>			
	A109	5,912,479	06/15/1999	Mori <i>et al.</i>			
	A110	5,943,560	08/24/1999	Chang <i>et al.</i>			
	A111	5,963,817	10/05/1999	Chu <i>et al.</i>			
	A112	5,966,622	10/12/1999	Levine <i>et al.</i>			
	A113	5,998,807	12/07/1999	Lustig <i>et al.</i>			
<b>EXAMINER</b>				<b>DATE CONSIDERED</b>			

<b>FORM PTO - 1449</b> <b>INFORMATION DISCLOSURE STATEMENT</b>				<b>ATTORNEY DOCKET NO.: ASC-066</b> <b>APPLICANT(S): Westhoff <i>et al.</i></b> <b>SERIAL NO.: 10/765,372</b> <b>FILING DATE: January 27, 2004 GROUP: 2812</b>			
<b>U.S. PATENT DOCUMENTS</b>							
<b>EXAM. INIT.</b>		<b>DOCUMENT NUMBER</b>	<b>DATE</b>	<b>NAME</b>	<b>CLASS</b>	<b>SUB CLASS</b>	<b>FILING DATE IF APPROPRIATE</b>
	A114	6,010,937	01/04/2000	Karam <i>et al.</i>			
	A115	6,013,134	01/11/2000	Chu <i>et al.</i>			
	A116	6,030,884	02/29/2000	Mori			
	A117	6,033,974	03/07/2000	Henley <i>et al.</i>			
	A118	6,033,995	03/07/2000	Muller			
	A119	6,039,803	03/21/2000	Fitzgerald <i>et al.</i>			
	A120	6,058,044	05/02/2000	Sugiura <i>et al.</i>			
	A121	6,059,895	05/09/2000	Chu <i>et al.</i>			
	A122	6,074,919	06/13/2000	Gardner <i>et al.</i>			
	A123	6,096,590	08/01/2000	Chan <i>et al.</i>			
	A124	6,103,559	08/15/2000	Gardner <i>et al.</i>			
	A125	6,107,653	08/22/2000	Fitzgerald			
	A126	6,111,267	08/29/2000	Fischer <i>et al.</i>			
	A127	6,117,750	09/12/2000	Bensahel <i>et al.</i>			
	A128	6,124,617	09/26/2000	Ryum <i>et al.</i>			
	A129	6,130,453	10/10/2000	Mei <i>et al.</i>			
	A130	6,133,799	10/17/2000	Favors <i>et al.</i>			
	A131	6,140,687	10/31/2000	Shimomura <i>et al.</i>			
	A132	6,143,636	11/07/2000	Forbes <i>et al.</i>			
	A133	6,153,495	11/28/2000	Kub <i>et al.</i>			
	A134	6,154,475	11/28/2000	Soref <i>et al.</i>			
	A135	6,160,303	12/12/2000	Fattaruso			
	A136	6,162,688	12/19/2000	Gardner <i>et al.</i>			
	A137	6,184,111	02/06/2001	Henley <i>et al.</i>			
	A138	6,191,006	02/20/2001	Mori			
	A139	6,191,007	02/20/2001	Matsui <i>et al.</i>			
	A140	6,191,432	02/20/2001	Sugiyama <i>et al.</i>			
	A141	6,194,722	02/27/2001	Fiorini <i>et al.</i>			
<b>EXAMINER</b>				<b>DATE CONSIDERED</b>			

<b>FORM PTO - 1449</b> <b>INFORMATION DISCLOSURE STATEMENT</b>		ATTORNEY DOCKET NO.: ASC-066 APPLICANT(S): Westhoff <i>et al.</i> SERIAL NO.: 10/765,372 FILING DATE: January 27, 2004 GROUP: 2812
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## U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	A142	6,204,529	03/20/2001	Lung <i>et al.</i>			
	A143	6,207,977	03/27/2001	Augusto			
	A144	6,210,988	04/03/2001	Howe <i>et al.</i>			
	A145	6,218,677	04/17/2001	Broekaert			
	A146	6,232,138	05/15/2001	Fitzgerald <i>et al.</i>			
	A147	6,235,567	05/22/2001	Huang			
	A148	6,242,324	06/05/2001	Kub <i>et al.</i>			
	A149	6,249,022	06/19/2001	Lin <i>et al.</i>			
	A150	6,251,755	06/26/2001	Furukawa <i>et al.</i>			
	A151	6,261,929	07/17/2001	Gehrke <i>et al.</i>			
	A152	6,266,278	07/24/2001	Harari <i>et al.</i>			
	A153	6,271,551	08/07/2001	Schmitz <i>et al.</i>			
	A154	6,271,726	08/07/2001	Fransis <i>et al.</i>			
	A155	6,291,321	09/18/2001	Fitzgerald			
	A156	6,313,016	11/06/2001	Kibbel <i>et al.</i>			
	A157	6,316,301	11/13/2001	Kant			
	A158	6,323,108	11/27/2001	Kub <i>et al.</i>			
	A159	6,329,063	12/11/2001	Lo <i>et al.</i>			
	A160	6,335,546	01/01/2002	Tsuda <i>et al.</i>			
	A161	6,339,232	01/15/2002	Takagi			
	A162	6,350,993	02/26/2002	Chu <i>et al.</i>			
	A163	6,352,909	03/05/2002	Usenko			
	A164	6,368,733	04/09/2002	Nishinaga			
	A165	6,372,356	04/16/2002	Thornton <i>et al.</i>			
	A166	6,399,970	06/04/2002	Kubo <i>et al.</i>			
	A167	6,403,975	06/11/2002	Brunner <i>et al.</i>			
	A168	6,406,589	06/18/2002	Yanagisawa			
	A169	6,407,406	06/18/2002	Tezuka			
EXAMINER				DATE CONSIDERED			

<b>FORM PTO - 1449</b> <b>INFORMATION DISCLOSURE STATEMENT</b>				<b>ATTORNEY DOCKET NO.: ASC-066</b> <b>APPLICANT(S): Westhoff <i>et al.</i></b> <b>SERIAL NO.: 10/765,372</b> <b>FILING DATE: January 27, 2004 GROUP: 2812</b>			
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	A170	6,420,937	07/16/2002	Akatsuka <i>et al.</i>			
	A171	6,425,951	07/30/2002	Chu <i>et al.</i>			
	A172	6,429,061	08/06/2002	Rim			
	A173	6,482,749	11/19/2002	Billington <i>et al.</i>			
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	B10	2 342 777	04/19/2000	GB				Y	Y
	B11	2-210816	08/22/1990	JP				N	Y (Abstract only)
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	B39	01/93338	12/06/2001	WO				N	Y
	B40	01/99169	12/27/2001	WO				N	Y
	B41	02/013262	02/14/2002	WO				N	Y
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	B47	02/071495	09/12/2002	WO				N	Y
	B48	02/082514	10/17/2002	WO				N	Y
	B49	03/015140	02/20/2003	WO				N	Y (Abstract only)
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